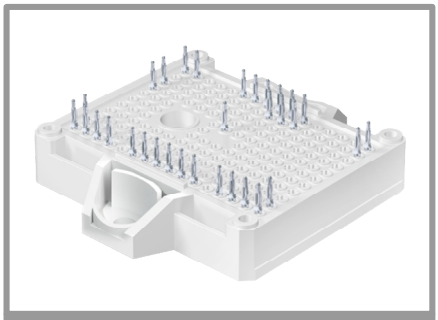
SK250MB120CR03TE2



SEMITOP®E2

Half-Bridge (Full SiC)

SK250MB120CR03TE2

Features*

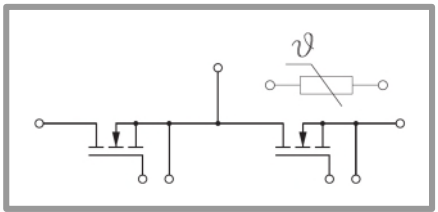
- Optimized design for superior thermal performance
- Extremely low inductance design
- Press-Fit contact technology
- 1200V Planar Gen3 SiC MOSFET
- Simple to drive with +15V gate voltage
- Optimized switching stability thanks to module integrated gate resistors
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Switched Mode Power Supplies
- Energy Storage Systems
- Electric Vehicle charging
- UPS
- Solar

Remarks

- Recommended T_{jop} = -40°C...+150°C
- Recommended turn-off / turn-on gate voltage V_{GS} = -4...0/+15V

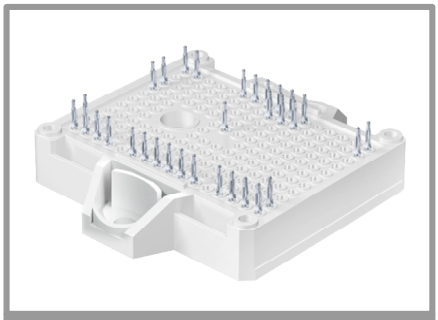


MB-T

Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
MOSFET				
V_{DSS}	T_j = 25 °C		1200	V
I_D	HPTP / HP-PCM Tj = 175 °C	T_s = 25 °C	267	A
		T_s = 70 °C	223	A
I_{DM}	Pulse witdh t_p limited by T_{vjmax}		720	A
V_{GS}	Transient Gate - Source voltage (t<100ns)		-8 ... 19	V
T_j			-40 ... 175	°C
Integrated body diode				
I_{FM}	Pulse width t_p limited by T_{vjmax}		720	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 150 °C		1076	A

Absolute Maximum Ratings			
Symbol	**Conditions**	**Values**	**Unit**
Module			
$I_{t(RMS)}$	$\Delta T_{terminal}$ at PCB joint = 30 K, per pin	30	A
T_{stg}	module without TIM	-40 ... 125	°C
V_{isol}	AC, sinusoidal, t = 1 min	2500	V

SK250MB120CR03TE2



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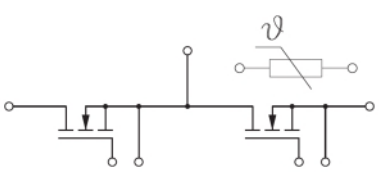


MB-T

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
MOSFET						
$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 0.6 mA, T_j = 25 °C		1200			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 69 mA, T_j = 25 °C		1.8	2.5	3.6	V
I_{DSS}	V_{GS} = 0 V, V_{DS} = 1200 V, T_j = 25 °C				0.6	mA
I_{GSS}	V_{DS} = 0 V, V_{GS} = 15 V, T_j = 25 °C				400	nA
$R_{DS(on)}$	V_{GS} = 15 V, I_D = 248 A, chiplevel	T_j = 25 °C		5.3	7.2	mΩ
		T_j = 150 °C		8.3		mΩ
C_{iss}	V_{GS} = 0 V, V_{DS} = 1000 V, T_j = 25 °C	f = 0.1 MHz		20400		pF
C_{oss}		f = 0.1 MHz		780		pF
C_{rss}		f = 0.1 MHz		60		pF
Q_G	V_{GS} = -4…15V, V_{DD} = 800V, I_D = 248 A			708		nC
R_{Gint}	T_j = 25 °C			2.3		Ω
$t_{d(on)}$	V_{DD} = 600 V I_D = 240 A V_{GS} = -4/+15 V $R_{G\ on/off}$ = 0.5 Ω di/dt_{off} = 15 kA/µs di/dt_{on} = 22 kA/µs dv/dt = 29 kV/µs L_s = 5 nH	T_j = 150 °C		49		ns
$t_{d(off)}$		T_j = 150 °C		120		ns
t_r		T_j = 150 °C		17		ns
t_f		T_j = 150 °C		29		ns
E_{on}		T_j = 150 °C		2.97		mJ
E_{off}		T_j = 150 °C		2.57		mJ
$R_{th(j-s)}$	per MOSFET, HPTP / HP-PCM			0.19		K/W
Integrated body diode						
$V_F = V_{SD}$	$-I_D$ = 124 A V_{GS} = -4 V chiplevel	T_j = 25 °C		4.6		V
		T_j = 150 °C		4.3		V
$V_{F0} = V_{SD0}$	chiplevel	T_j = 25 °C		3.8		V
		T_j = 150 °C		3.6		V
$r_F = r_{SD}$	chiplevel	T_j = 25 °C		6.4		mΩ
		T_j = 150 °C		5.6		mΩ
t_{rr}	V_{DD} = 600 V $-I_D$ =240 A V_{GS} =-4 V R_{Gon} = 0.5 Ω di/dt_{off} = 23 kA/µs	T_j = 150 °C		40		µs
Q_{rr}		T_j = 150 °C		6.7		µC
I_{rr}		T_j = 150 °C		337		A
E_{rr}		T_j = 150 °C		2.21		mJ

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Module					
L_{CE}			6		nH
M_s	to heatsink	1.6		2.3	Nm
w	weight		35		g

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Temperature Sensor					
R_{100}	T_r = 100 °C		493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}*\exp[B_{100/125}*(1/T-1/T_{100})]$, T[K];		3550 (± 2%)		K

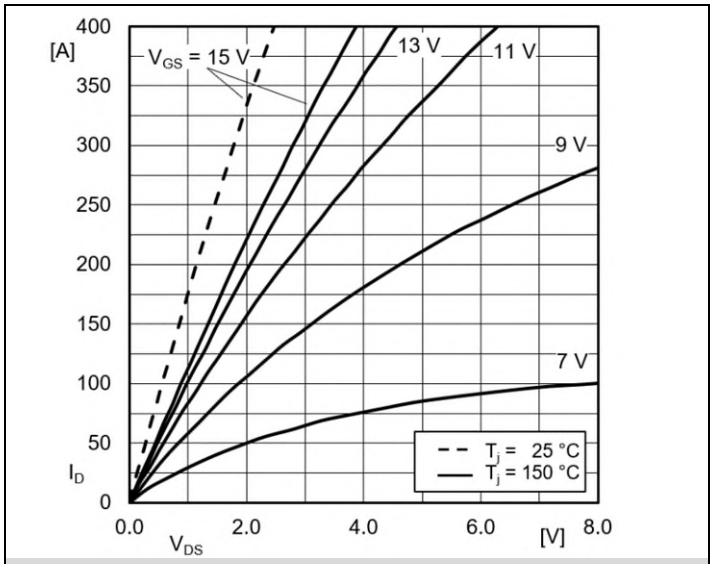


Fig.1: Typ. MOSFET forward output characteristic, incl. $R_{DD'+SS'}$

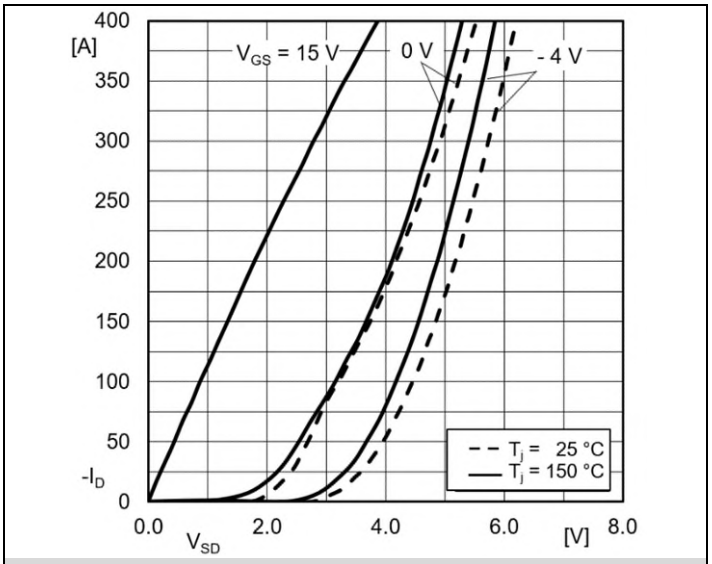


Fig. 1a: Typ. MOSFET reverse output characteristic, incl. $R_{DD'+SS'}$

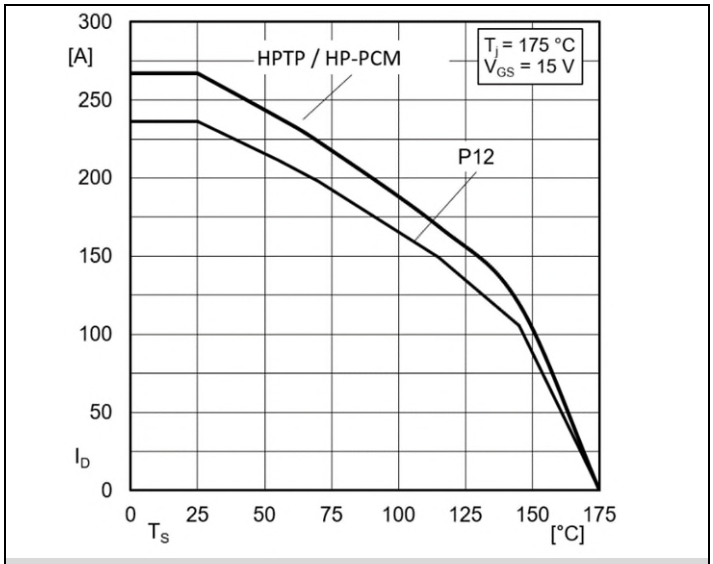


Fig. 2: MOSFET Rated current vs. temperature $I_D = f(T_S)$

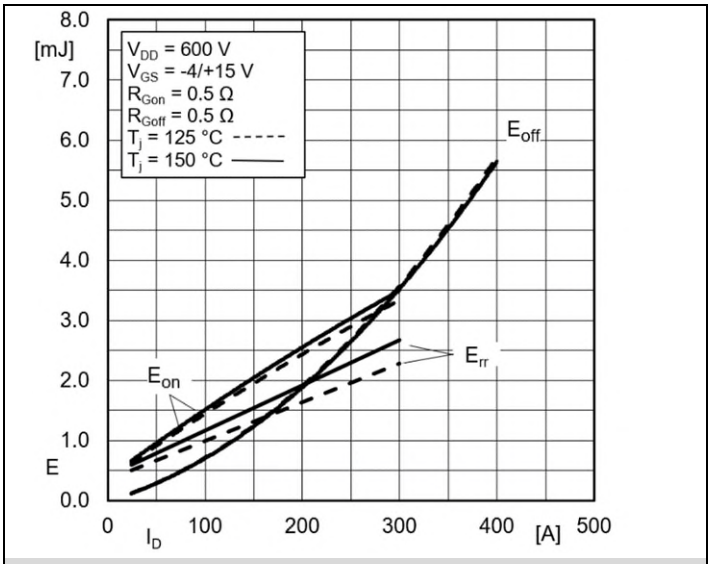


Fig. 3: Typ. MOSFET switching energy $E = f(I_D)$ at R_{G1}

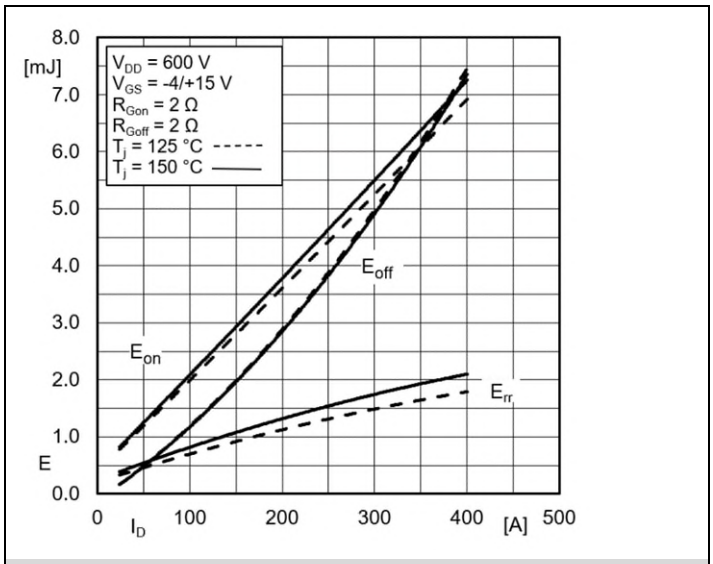


Fig. 3a: Typ. MOSFET switching energy $E = f(I_D)$ at R_{G2}

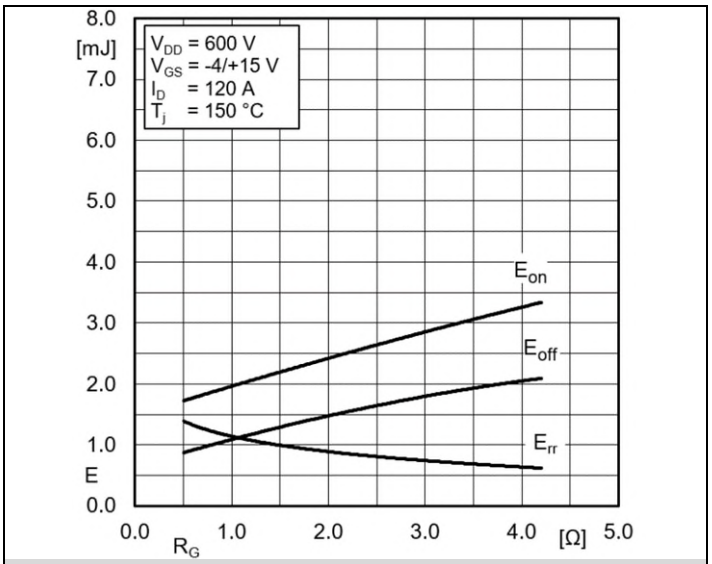


Fig. 4: Typ. MOSFET switching energy $E = f(R_G)$ at I_{D1}

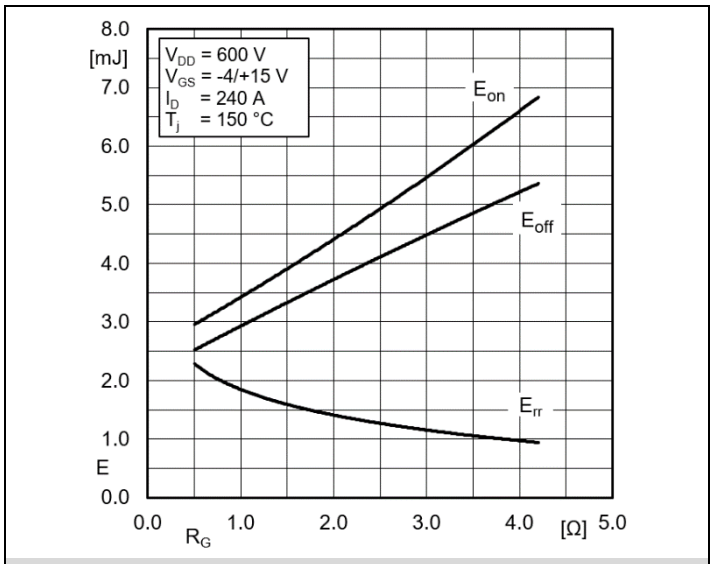


Fig. 4a: Typ. MOSFET switching energy E = f (R_G) at I_{D2}

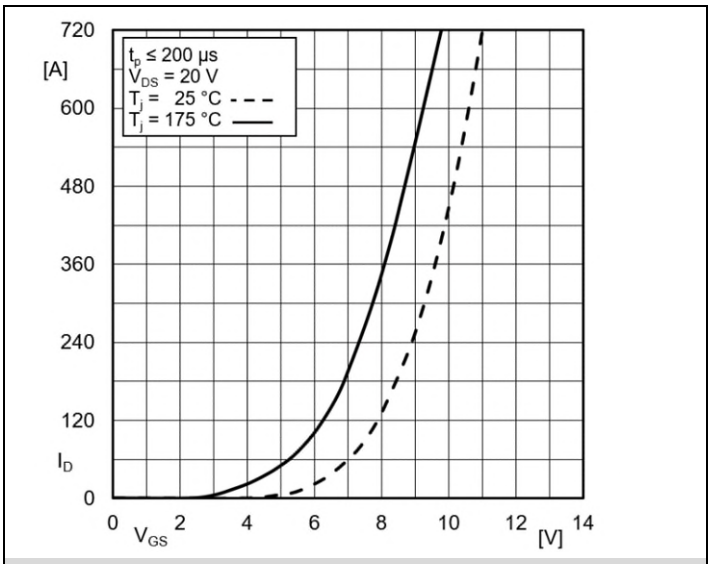


Fig. 5: Typ. MOSFET transfer characteristic

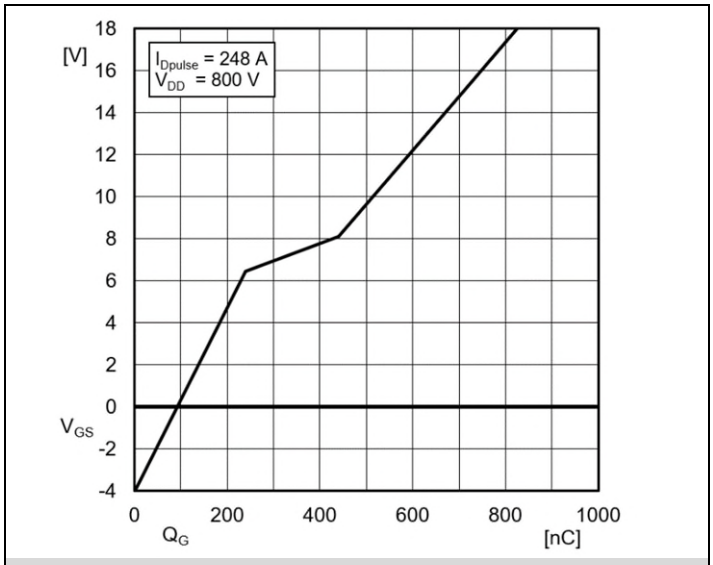


Fig. 6: Typ. MOSFET gate charge characteristic

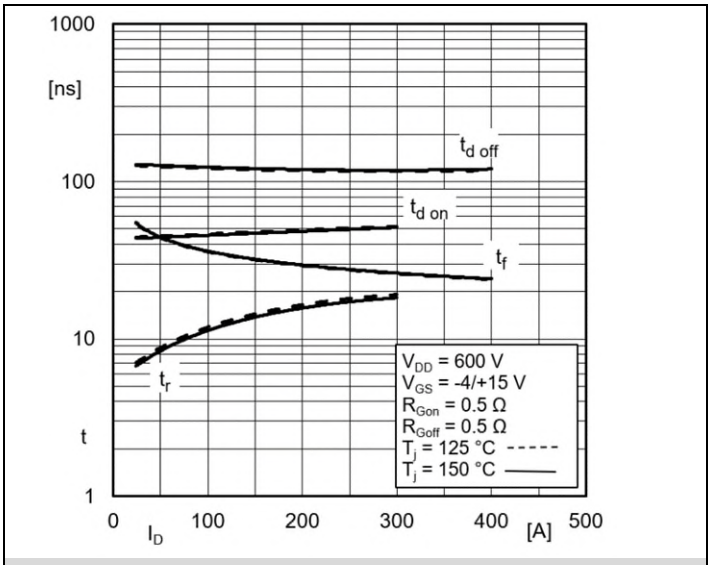


Fig. 7: Typ. MOSFET switching times t = f (I_D) at R_{G1}

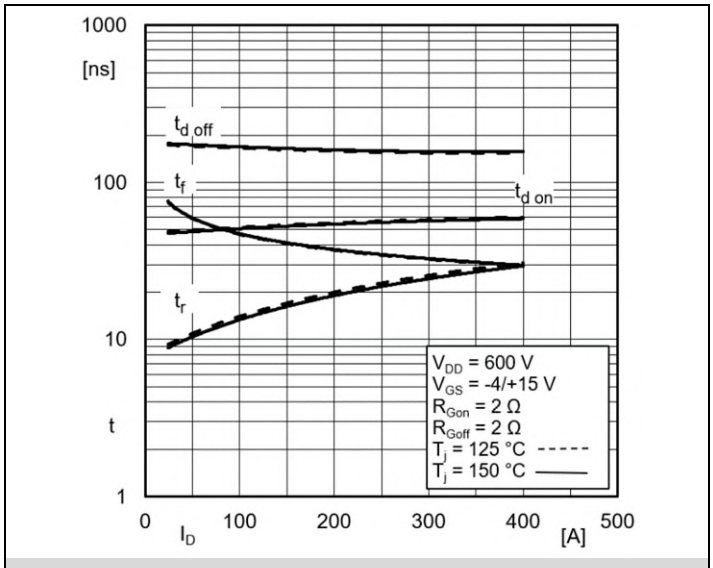


Fig. 7a: Typ. MOSFET switching times t = f (I_D) at R_{G2}

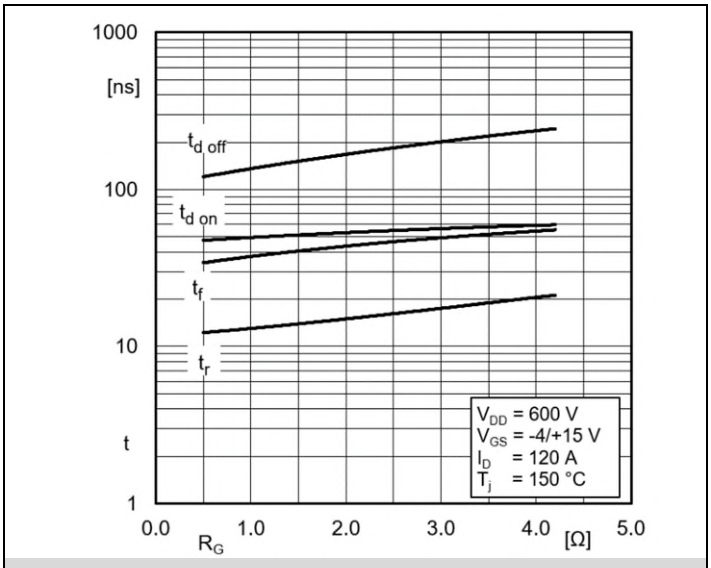


Fig. 8: Typ. MOSFET switching times t = f (R_G) at I_{D1}

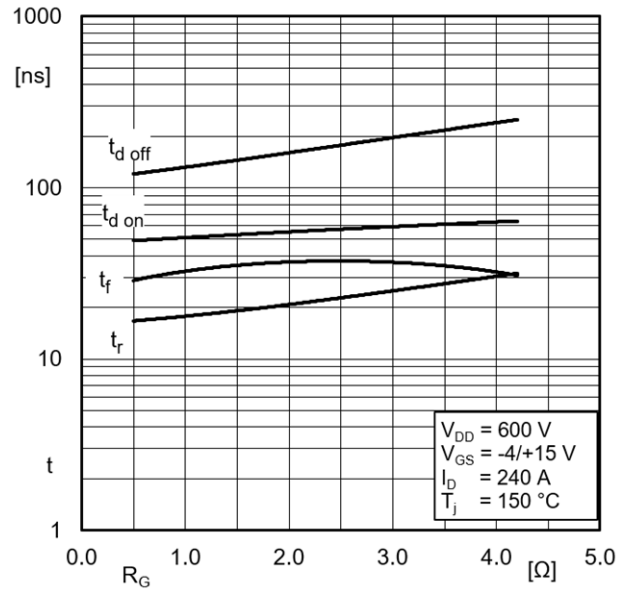


Fig. 8a: Typ. MOSFET switching times t = f (R_G) at I_{D2}

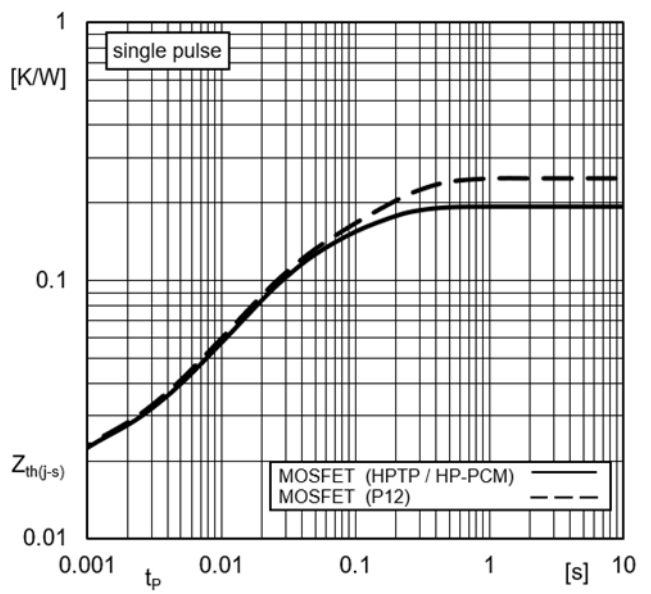


Fig. 9: Typ. transient thermal impedance

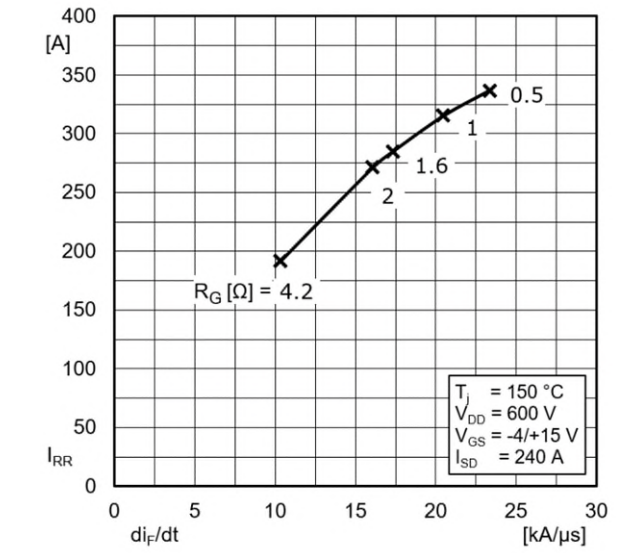


Fig. 10: Typ. body diode peak reverse recovery current I_{RR} = f (di_F/dt)

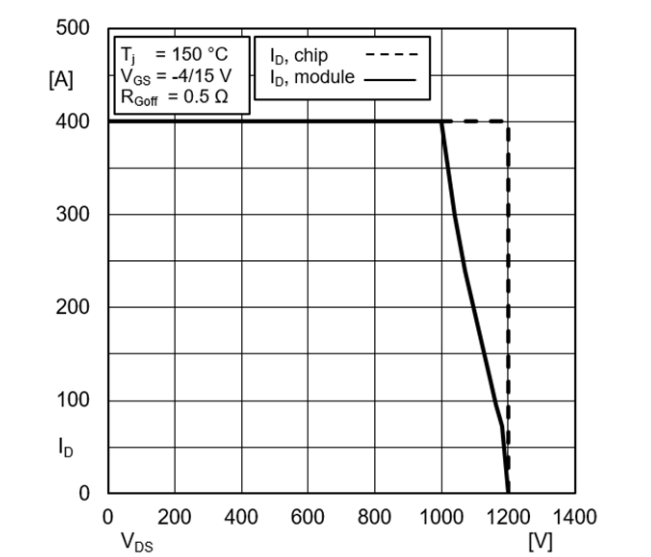
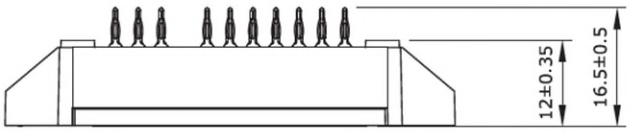
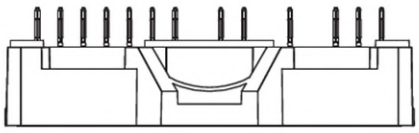
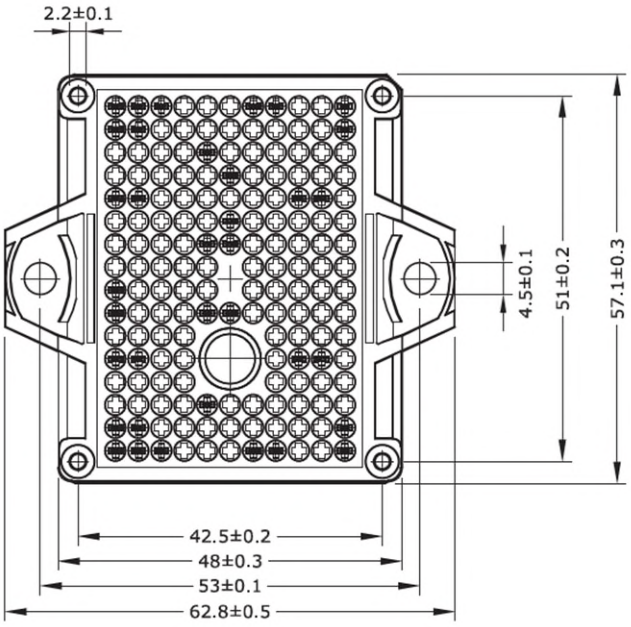
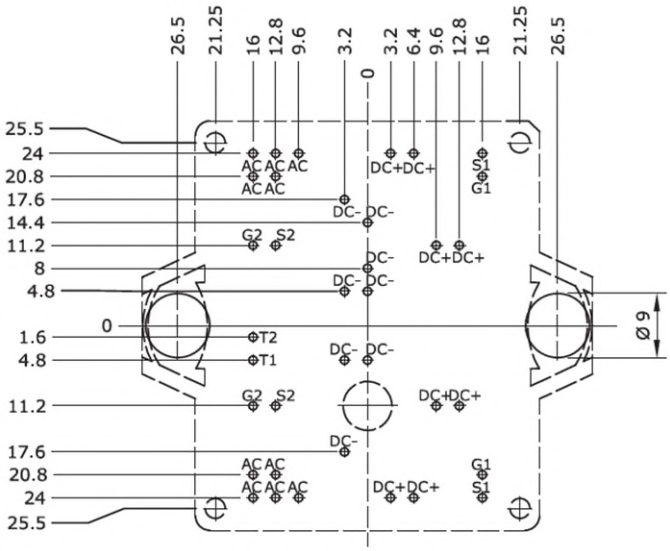


Fig. 11: MOSFET Reverse Bias Safe Operating Area (RBSOA)



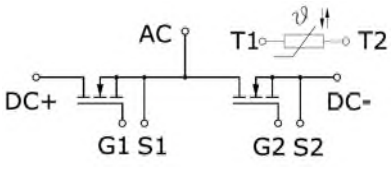






- Pin-Grid 3.2 mm
- Tolerance of PCB hole pattern ⌖ Ø0.1
- Diameters of drill ∅ 1.15mm
- Copper thickness in hole 25 - 50 µm
- Hole specification for contacts:
  refer to SEMITOP E1/E2 Mounting Instruction

Pinout and Dimensions



MB-T

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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